

Band switching diode

DAN235E / DAN235U

● Applications

High frequency switching

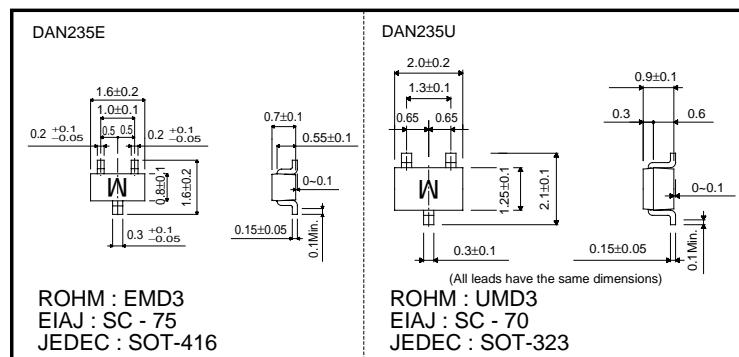
● Features

- 1) Small surface mounting type.
(EMD3, UMD3)
- 2) High reliability.

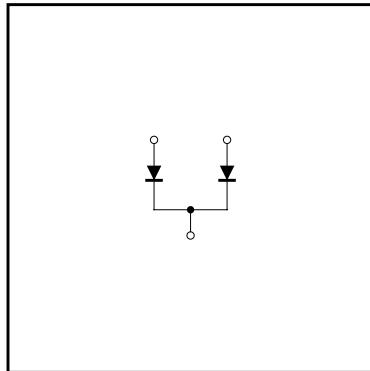
● Construction

Silicon epitaxial planar

● External dimensions (Units : mm)



● Circuit



● Absolute maximum ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	35	V
Power dissipation	P_d	150	mW
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55~+125	°C

Diodes

● Electrical characteristics ($T_a=25^\circ C$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	0.85	1.0	V	$I_F=10mA$
Reverse current	I_R	—	0.01	10	nA	$V_R=25V$
Capacitance between terminals	C_T	—	0.87	1.2	pF	$V_R=6V, f=1MHz$
Forward operating resistance	r_F	—	0.65	0.9	Ω	$I_F=2mA, f=100MHz$

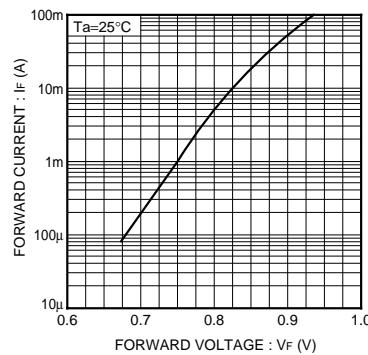
● Electrical characteristic curves ($T_a=25^\circ C$)

Fig. 1 Forward characteristics

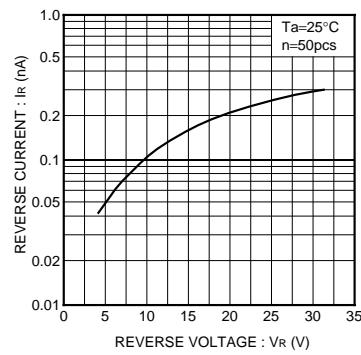


Fig. 2 Reverse characteristics

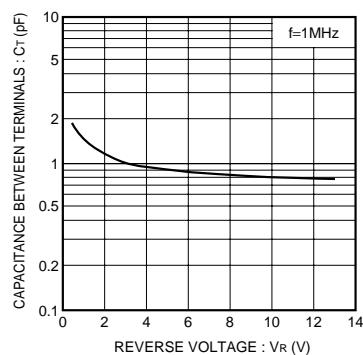


Fig. 3 Capacitance between terminals characteristics

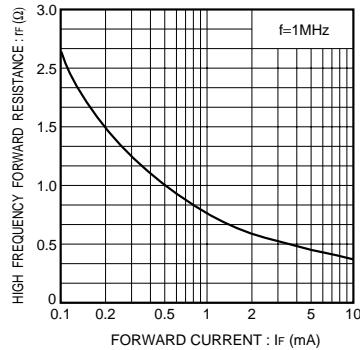
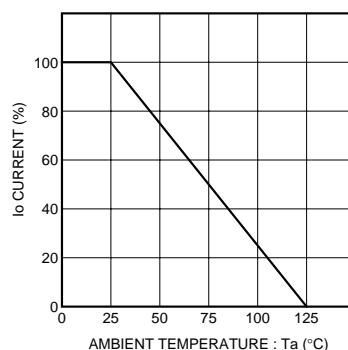


Fig. 4 Forward operating resistance characteristics

Fig. 5 Derating curve
(mounting on glass epoxy PCBs)